

P-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^d	Q _g (Typ)			
- 60	0.060 at V _{GS} = - 10 V	- 19	26			
- 60	0.077 at V _{GS} = - 4.5 V	- 16.8	20			

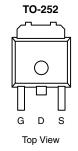
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % UIS Tested
- Compliant to RoHS Directive 2002/95/EC

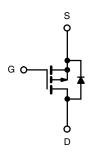


APPLICATIONS

- · High Side Switch for Full Bridge Converter
- DC/DC Converter for LCD Display



Drain Connected to Tab



P-Channel MOSFET

Ordering Information:	SUD19P06-60-E3 (Lead (Pb)-free	э)

SUD19P06-60-GE3 (Lead (Pb)-free and Halogen free)

ABSOLUTE MAXIMUM RATINGS (T_A)	= 25 °C, unless otherw	rise note)			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	- 60	V		
Gate-Source Voltage	V _{GS}	± 20	\ \ \ \ \		
Continuous Drain Current (T _{.1} = 150 °C)	T _C = 25 °C	I _D	- 18.3	Δ.	
Continuous Diam Current (1) = 130 C)	T _C = 125 °C	' ^b	- 8.19		
Pulsed Drain Current	I _{DM}	- 30	A		
Avalanche Current, Single Pulse		I _{AS}	- 22	1	
Repetitive Avalanche Energy, Single Pulse ^a	L = 0.1 mn	E _{AS}	24.2	mJ	
Dower Discipation	T _C = 25 °C	P _D	38.5 ^c	w	
Power Dissipation	T _A = 25 °C	' 0	2.3 ^{b, c}		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Marrian una lumation de Anabiando	t ≤ 10 s	R _{thJA}	17	21	1	
Maximum Junction-to-Ambient ^D	Steady State		45	55	°C/W	
Maximum Junction-to-Case		R _{thJC}	2.7	3.25		

Notes:

- a. Duty cycle \leq 1 %.
- b. When mounted on 1" square PCB (FR-4 material).
- c. See SOA curve for voltage derating.
- d. Based up on T_C = 25 °C.



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Parameter	Symbol	Symbol Test Conditions		Min . Typ.		Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	- 60			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1		- 3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
	I _{DSS}	$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}$			- 1	μΑ	
Zero Gate Voltage Drain Current		$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 ^{\circ}\text{C}$			- 50		
		$V_{DS} = -60 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 150 ^{\circ} \text{ C}$			- 125		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 30			Α	
		V _{GS} = - 10 V, I _D = - 10 A		0.048	0.060	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -10 \text{ V}, I_D = -10 \text{ A}, T_J = 125 \text{ °C}$			0.102		
Dialii-Source Oil-State Hesistance	' 'DS(on)	V _{GS} = - 10 V, I _D = - 10 A, T _J = 150 °C			0.120	52	
		$V_{GS} = -4.5 \text{ V}, I_D = -5 \text{ A}$		0.061	0.077		
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 15 V, I _D = - 10 A		22		S	
Dynamic ^b							
Input Capacitance	C _{iss}			1140	1710	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = -25 \text{ V}, f = 1 \text{ MHz}$		130			
Reverse Transfer Capacitance	C _{rss}			90			
Total Gate Charge ^c	Q_g			26	40	nC	
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = -30 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -10 \text{ A}$		4.5			
Gate-Drain Charge ^c	Q_{gd}			7			
Gate Resistance	R _g	f = 1 MHz		7		Ω	
Turn-On Delay Time ^c	t _{d(on)}			8	15		
Rise Time ^c	t _r	V_{DD} = - 30 V, R_L = 3 Ω		9	15		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong -19 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 2.5 \Omega$		65	100	ns	
Fall Time ^c	t _f]		30	45		
Drain-Source Body Diode and Characte	eristics (T _C = 2	5 °C) ^b					
Continuous Current	I _S				- 30		
Pulsed Current	I _{SM}				- 30	A	
Forward Voltage ^a	V _{SD}	I _F = - 19 A, V _{GS} = 0 V		- 1	- 1.5	V	
Reverse Recovery Time		I _F = - 19 A, di/dt = 100 A/μs		41	61	ns	

Notes

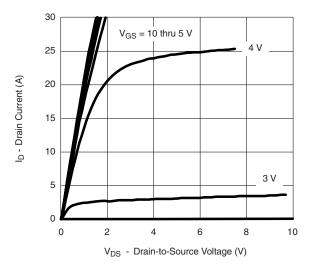
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

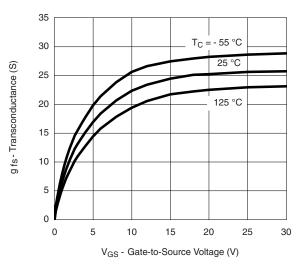


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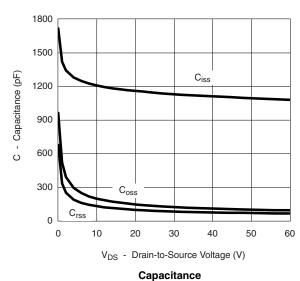
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

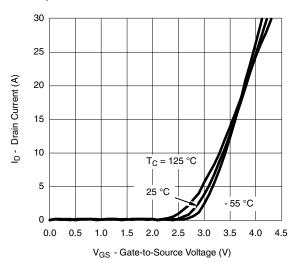


Output Characteristics

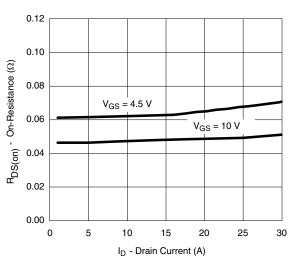


Transconductance

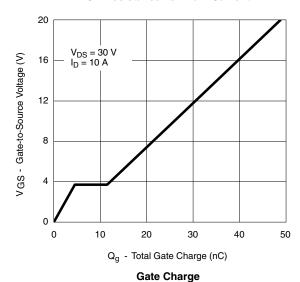




Transfer Characteristics



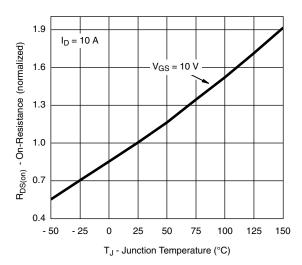
On-Resistance vs. Drain Current



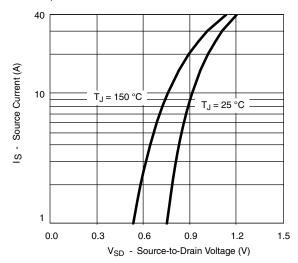


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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

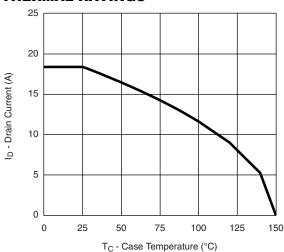


On-Resistance vs. Junction Temperature

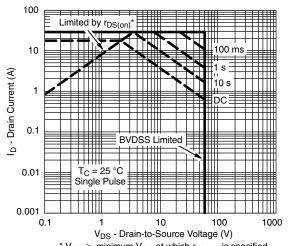


Source-Drain Diode Forward Voltage

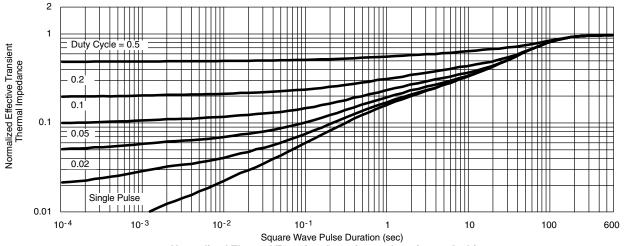
THERMAL RATINGS



Maximum Drain Current vs. Case Temperature



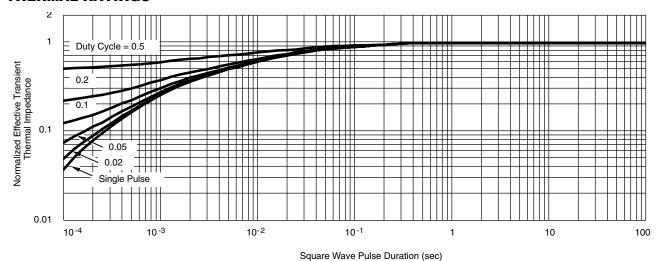
* V_{GS} > minimum V_{GS} at which r_{DS(on)} is specified **Safe Operating Area**



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS

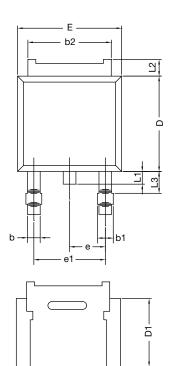


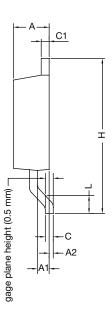
Normalized Thermal Transient Impedance, Junction-to-Case



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TO-252AA CASE OUTLINE





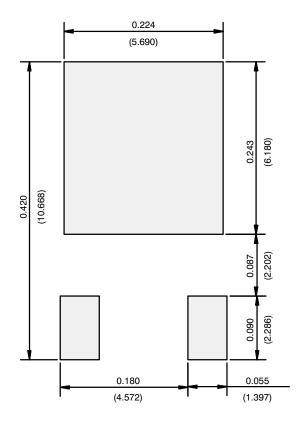
	MILLIMETERS		INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
Е	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28 BSC		0.090 BSC		
e1	4.57	BSC	0.180	BSC	
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11-0110-Rev. L, 18-Apr-11 DWG: 5347					

Note

• Dimension L3 is for reference only.

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RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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